

SILICON NPN TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

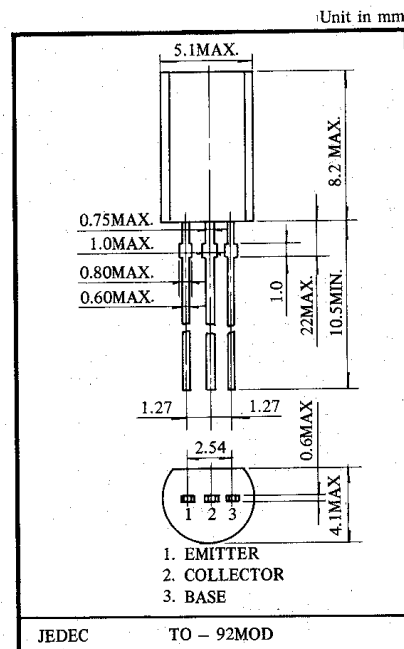
KTC 2235

APPLICATIONS

- Audio Power Amplifier Applications.
- Driver Stage Amplifier Applications.

FEATURES

- Complementary to KTA 965



■ MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V	Emitter Current	I_E	-800	mA
Collector-Emitter Voltage	V_{CEO}	120	V	Collector Dissipation	P_C	900	mW
Emitter-Base Voltage	V_{EBO}	5	V	Junction Temperature	T_j	150	°C
Collector Current	I_C	800	mA	Storage Temperature	T_{stg}	-55 ~ 150	°C

■ ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB}=120\text{ V}, I_E=0$	—	—	100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$	—	—	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10\text{ mA}, I_B=0$	120	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1\text{ mA}, I_C=0$	5	—	—	V
DC Current Gain	h_{FE}	$V_{CE}=5\text{ V}, I_C=100\text{ mA}$	80	—	240	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{ mA}, I_B=50\text{ mA}$	—	—	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5\text{ V}, I_C=500\text{ mA}$	—	—	1.0	V
Transition Frequency	f_T	$V_{CE}=5\text{ V}, I_C=100\text{ mA}$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{ V}, I_E=0, f=1\text{ MHz}$	—	—	30	pF

■ NOTE: According to h_{FE} , Classified as follows.

0	80-160	Y	120-240
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